

STRAINED SILICON MOSFET HAVING IMPROVED CARRIER MOBILITY, STRAINED SILICON
CMOS DEVICE, AND METHODS OF THEIR FORMATION

Inventors: Qi XIANG

Attorney: Ronald Coslick - 039153-0667 (AMD H0981)

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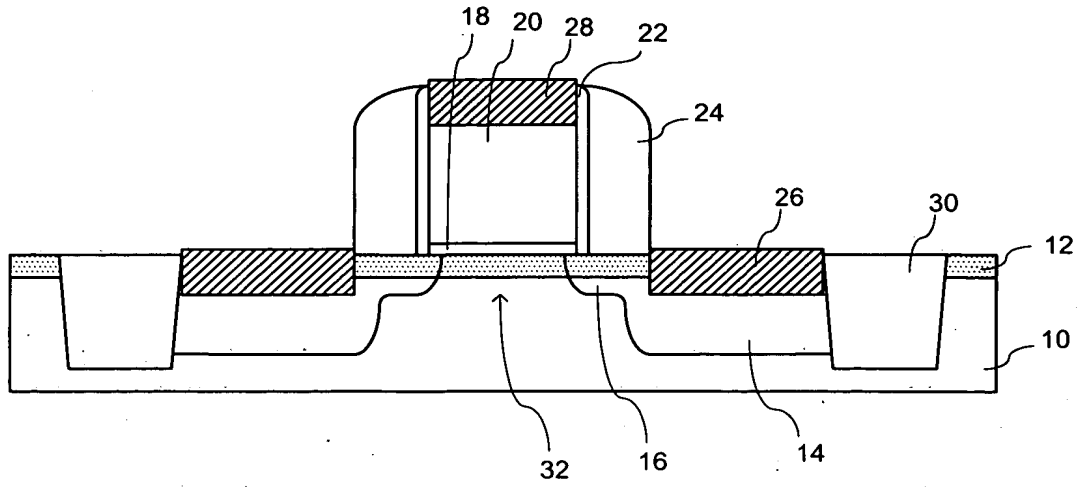


Figure 1

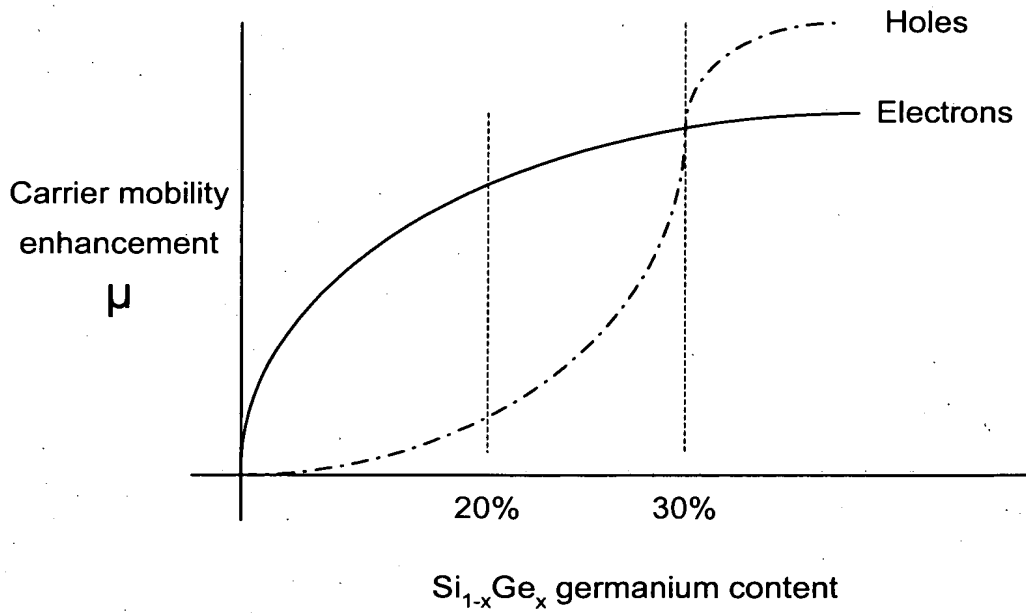


Figure 2

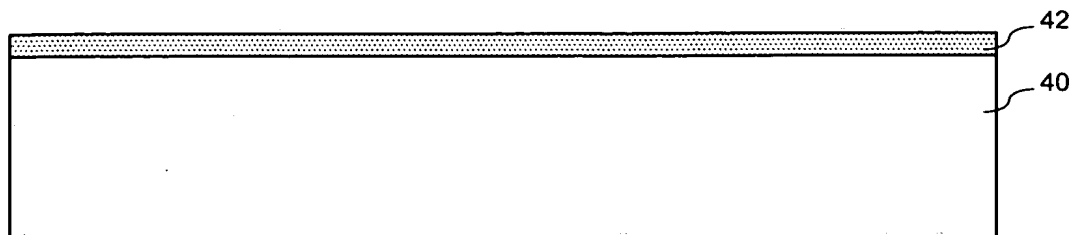


Figure 3a

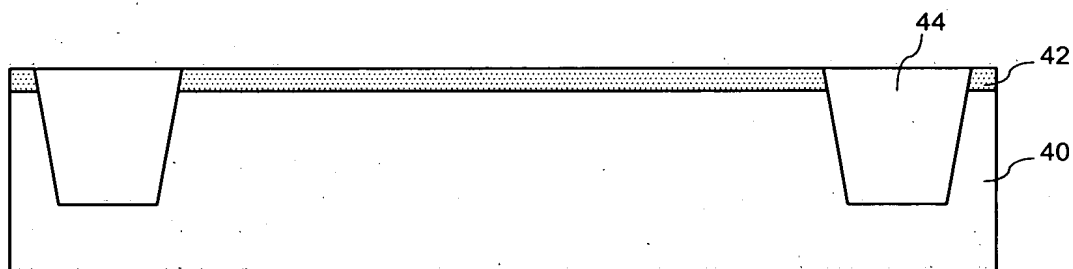


Figure 3b

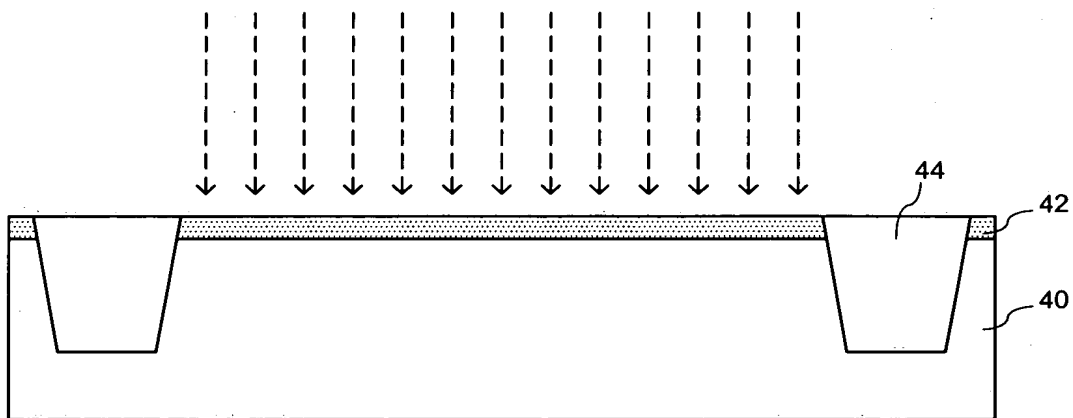


Figure 3c

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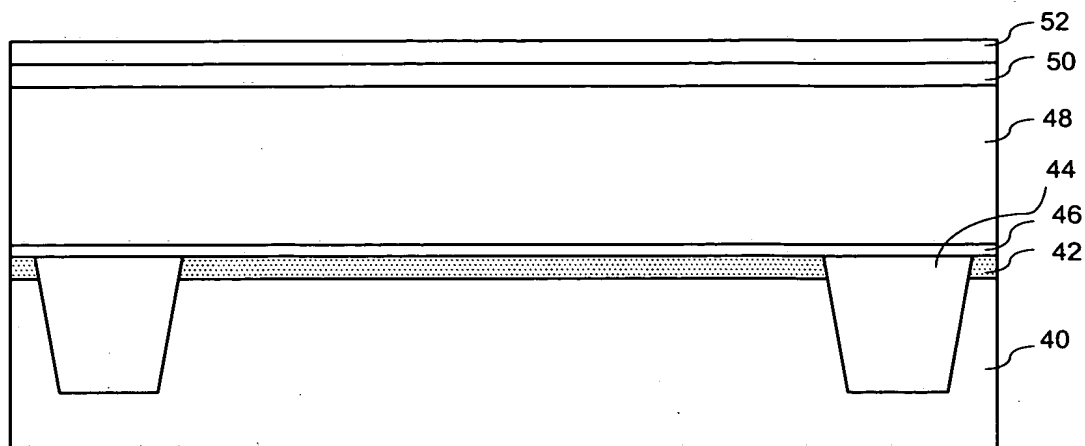


Figure 3d

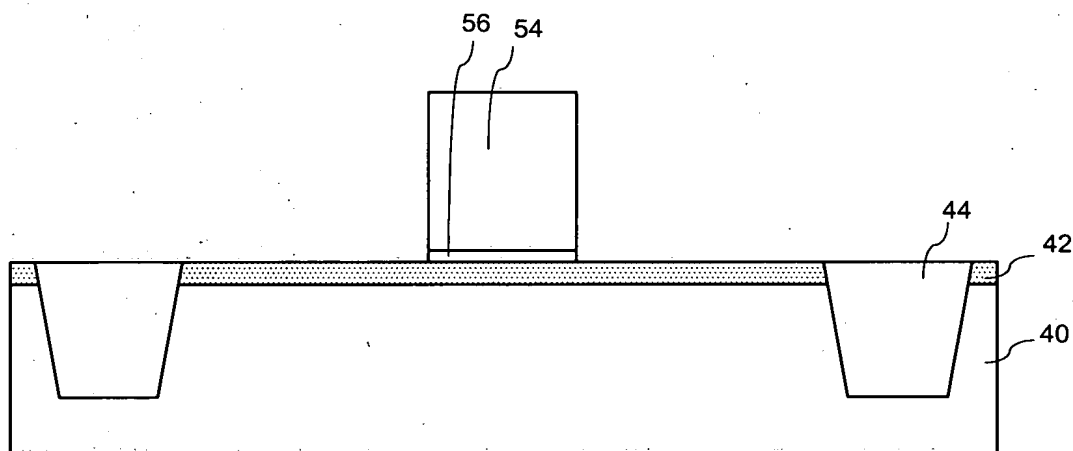


Figure 3e

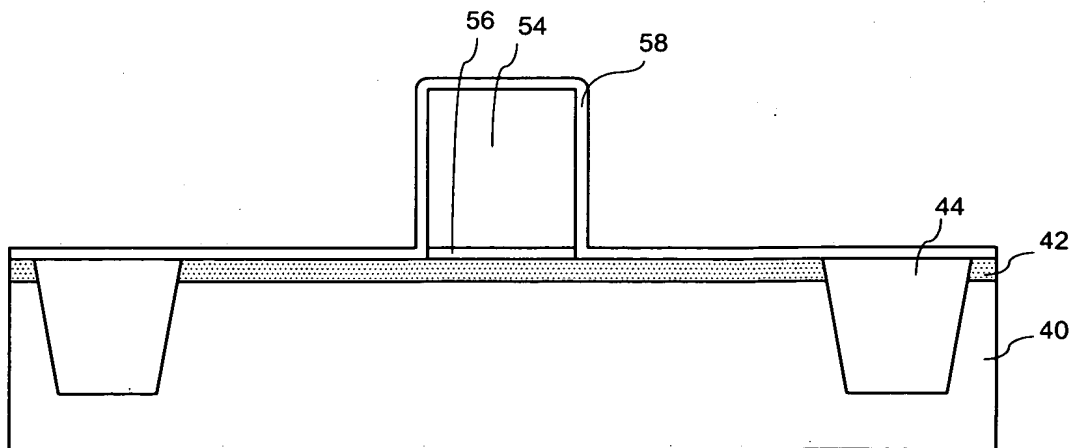


Figure 3f

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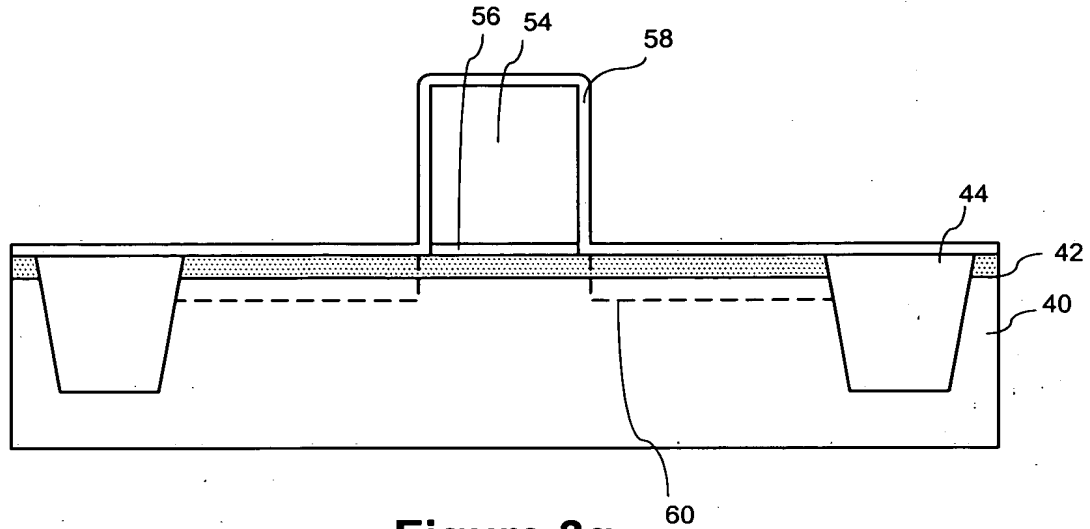


Figure 3g

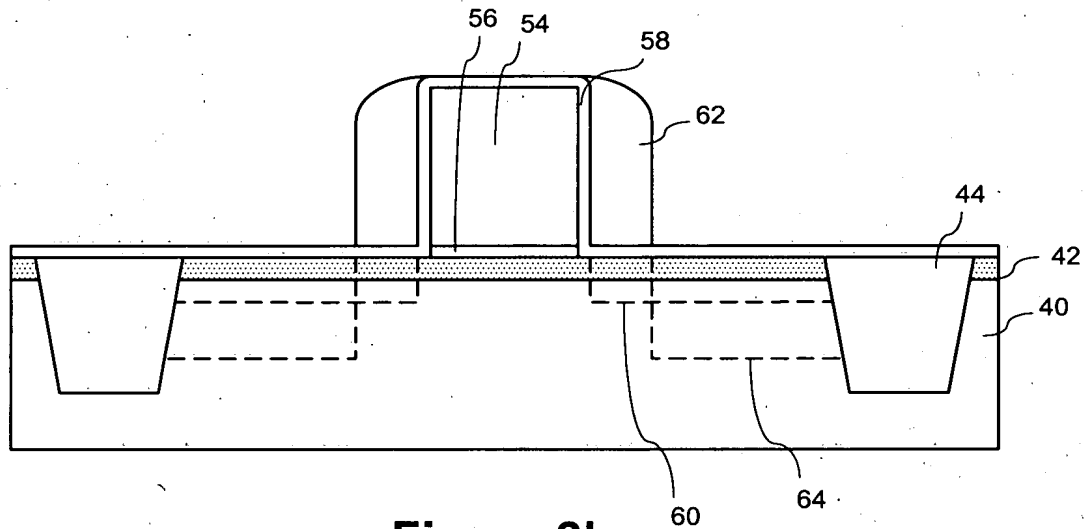


Figure 3h

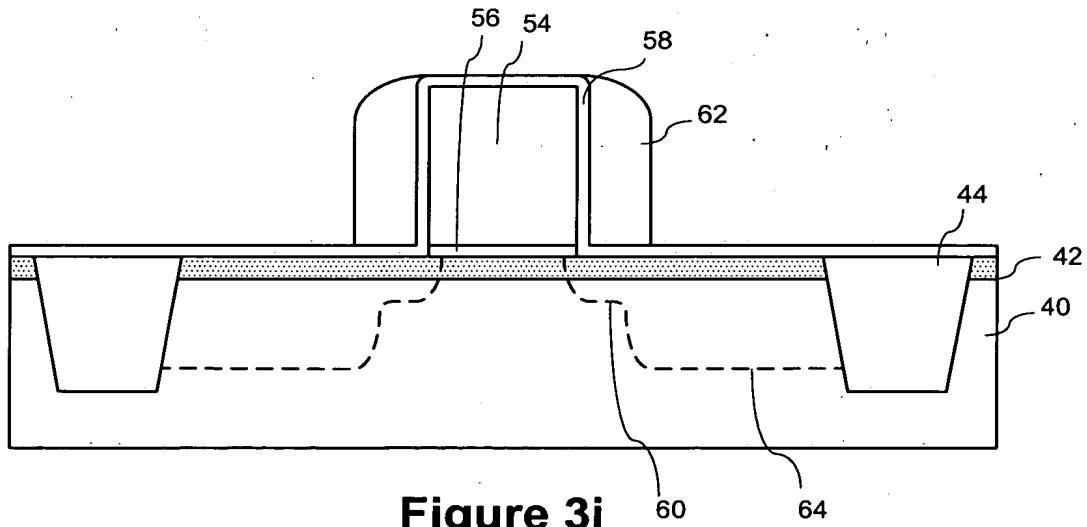


Figure 3i

STRAINED SILICON MOSFET HAVING IMPROVED CARRIER MOBILITY, STRAINED SILICON
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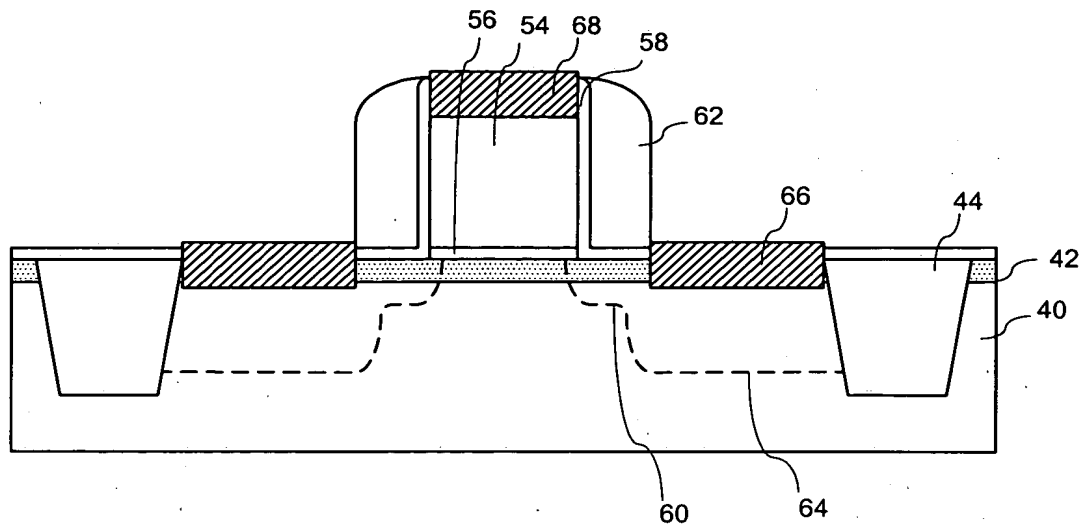


Figure 3j

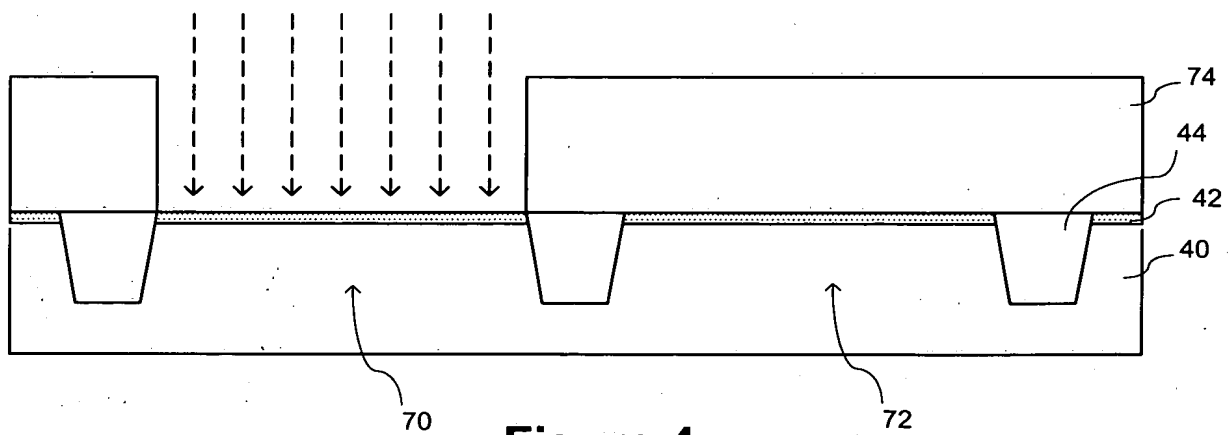


Figure 4

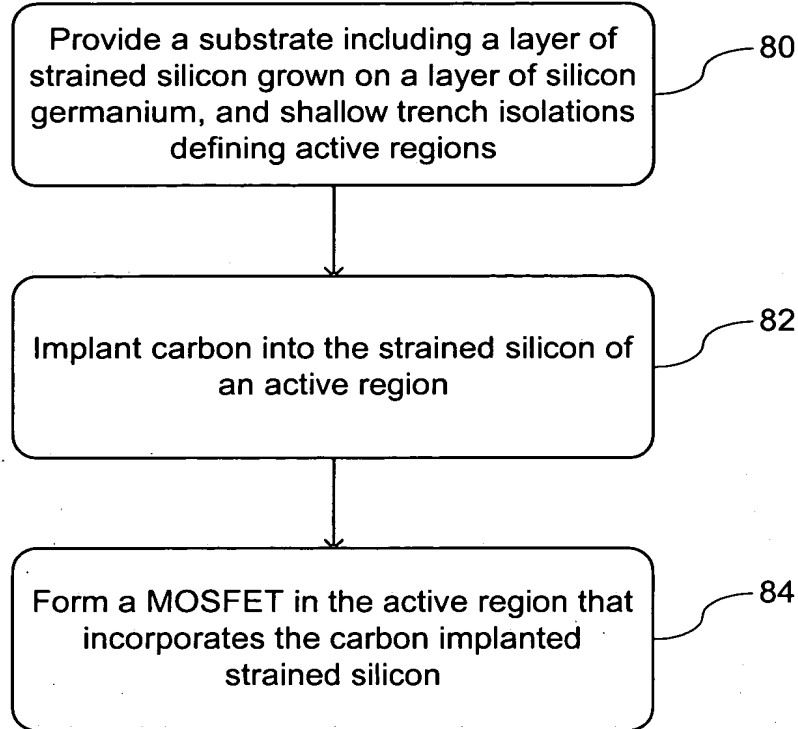


Figure 5

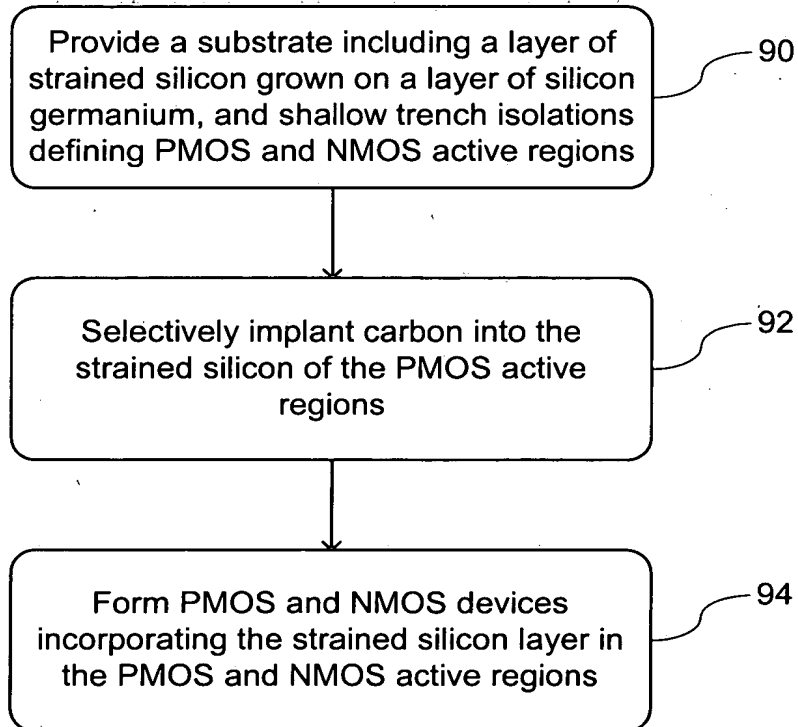


Figure 6